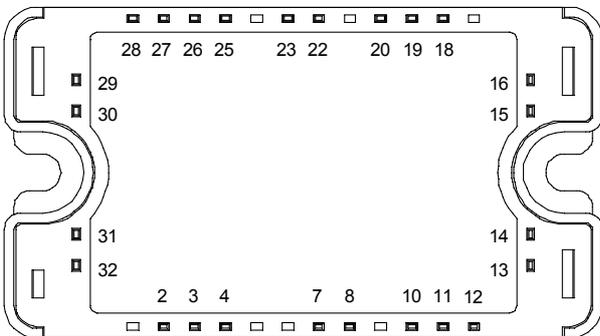
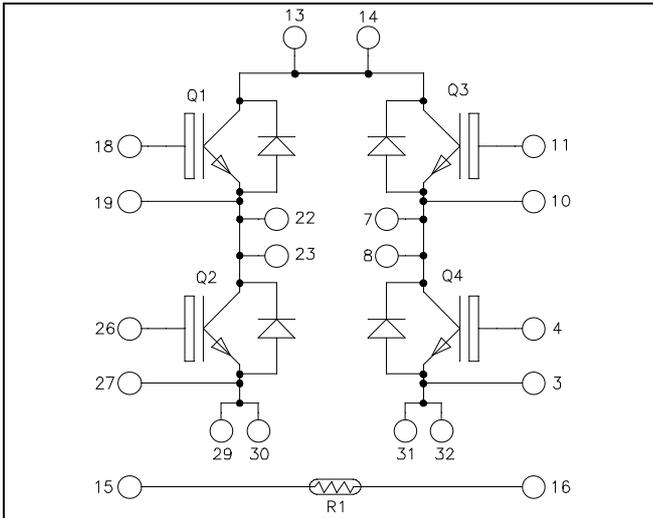


**Full - Bridge
Trench + Field Stop IGBT3
Power Module**

**$V_{CES} = 1700V$
 $I_C = 30A @ T_c = 80^\circ C$**



All multiple inputs and outputs must be shorted together
 Example: 13/14 ; 29/30 ; 22/23 ...

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Easy paralleling due to positive TC of VCEsat
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1700	V
I_C	Continuous Collector Current	$T_c = 25^\circ C$	45
		$T_c = 80^\circ C$	30
I_{CM}	Pulsed Collector Current	$T_c = 25^\circ C$	70
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	210
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$	60A@1600V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1700V$			250	μA
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15V$ $I_C = 30A$		2.0 2.4	2.4	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1.5mA$	5.2	5.8	6.4	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			600	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V, V_{CE} = 25V$		2500		pF
C_{res}	Reverse Transfer Capacitance	$f = 1MHz$		90		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15V$ $V_{Bus} = 900V$ $I_C = 30A$ $R_G = 18\Omega$		100		ns
T_r	Rise Time			70		
$T_{d(off)}$	Turn-off Delay Time			650		
T_f	Fall Time			80		
$T_{d(on)}$	Turn-on Delay Time		Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 900V$ $I_C = 30A$ $R_G = 18\Omega$		100	
T_r	Rise Time			70		
$T_{d(off)}$	Turn-off Delay Time			750		
T_f	Fall Time			100		
E_{on}	Turn-on Switching Energy				17	
E_{off}	Turn-off Switching Energy			15		

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		1700			V	
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1700V$			250 500	μA	
I_F	DC Forward Current	$T_C = 80^\circ\text{C}$		50		A	
V_F	Diode Forward Voltage	$I_F = 50A$ $V_{GE} = 0V$		1.8 1.9	2.2	V	
t_{rr}	Reverse Recovery Time	$I_F = 50A$ $V_R = 900V$ $di/dt = 800A/\mu\text{s}$		385 490		ns	
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$		14		μC
			$T_j = 125^\circ\text{C}$		23		
E_r	Reverse Recovery Energy			6 12		mJ	
		$T_j = 125^\circ\text{C}$					

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C		50		k Ω
$B_{25/85}$	$T_{25} = 298.15\text{K}$		3952		K

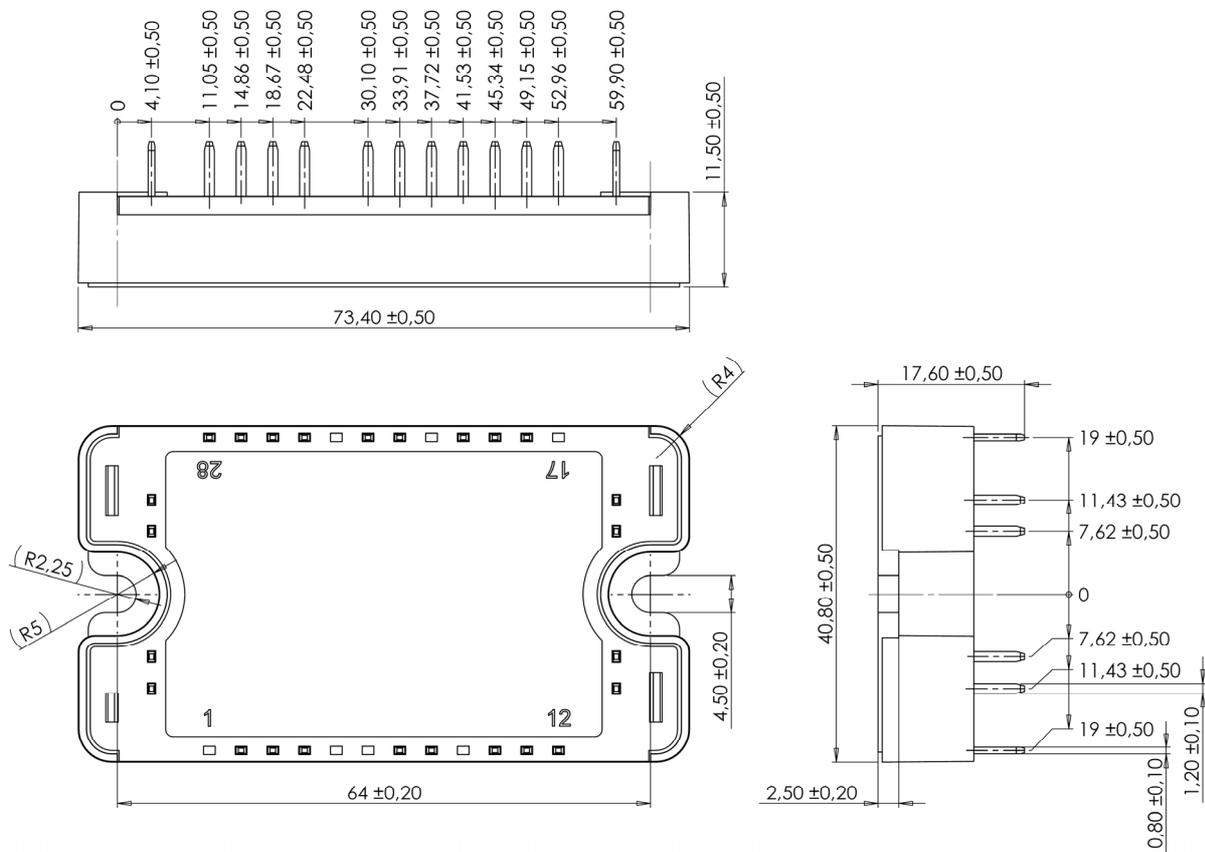
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
 R_T : Thermistor value at T

Thermal and package characteristics

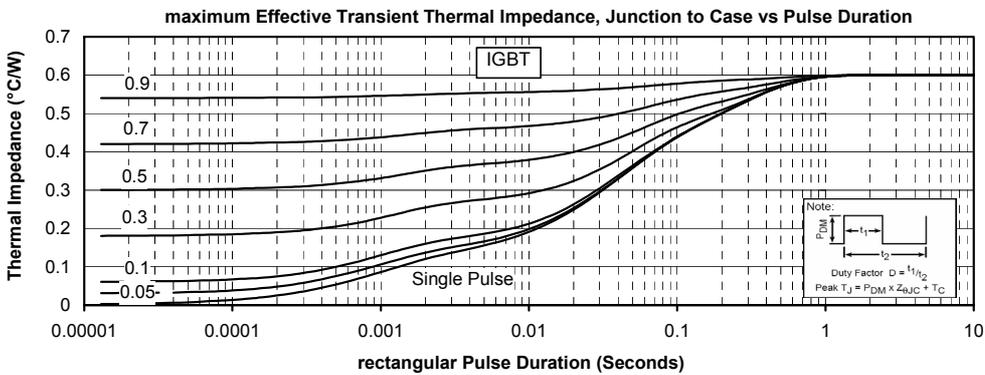
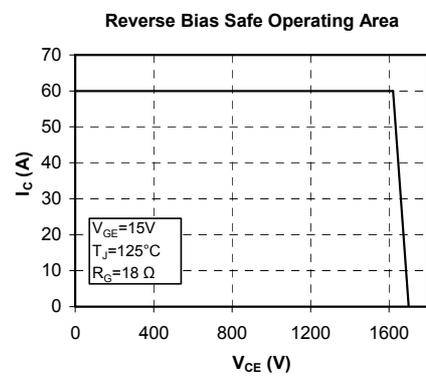
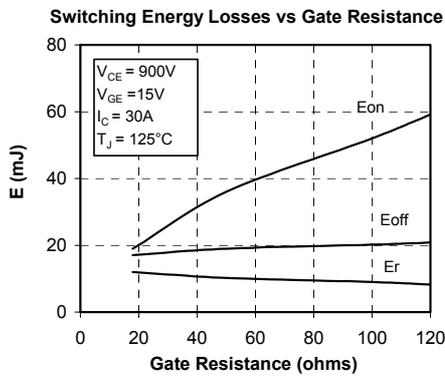
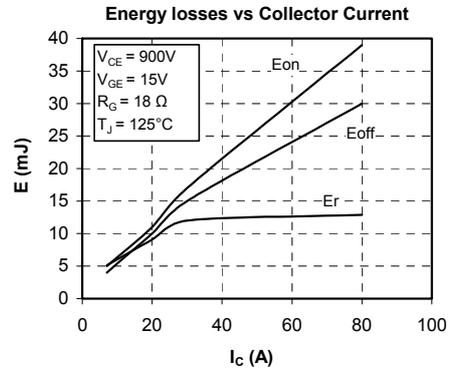
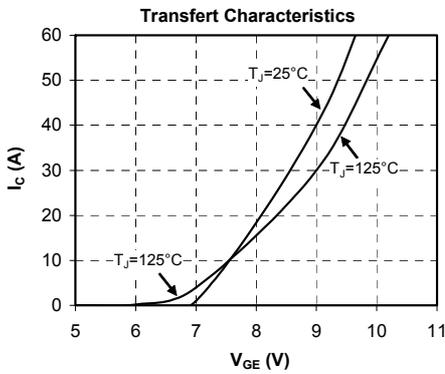
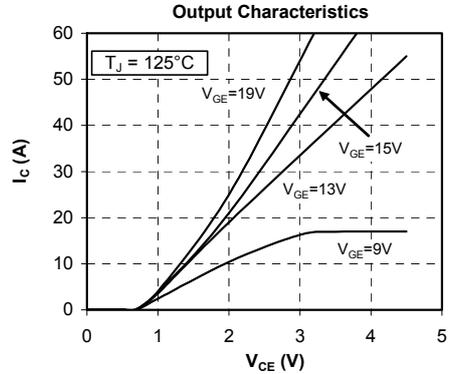
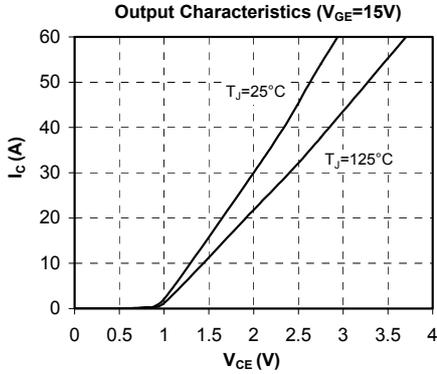
Symbol	Characteristic	Min	Typ	Max	Unit	
R _{thJC}	Junction to Case Thermal Resistance	IGBT		0.6	°C/W	
		Diode		0.7		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz	4000			V	
T _J	Operating junction temperature range	-40		150	°C	
T _{STG}	Storage Temperature Range	-40		125		
T _C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

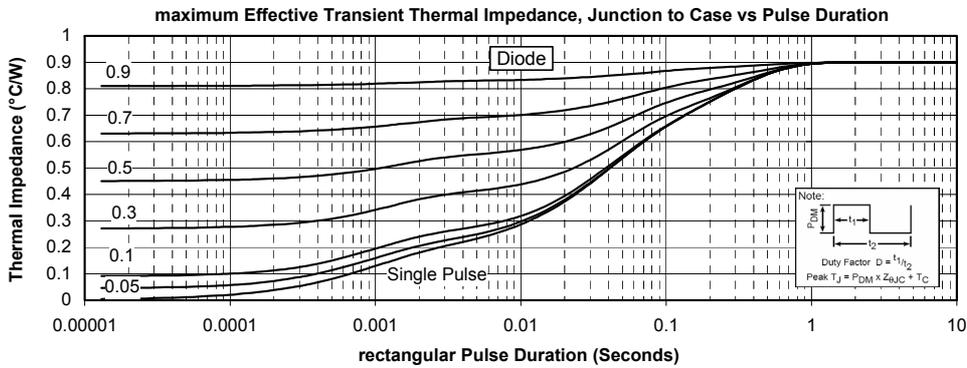
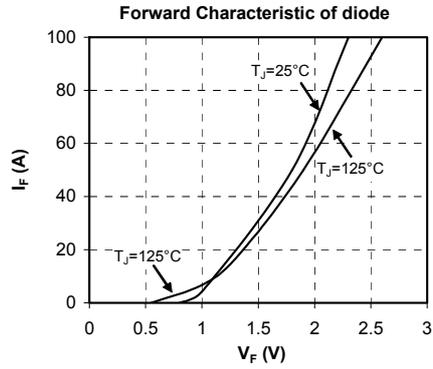
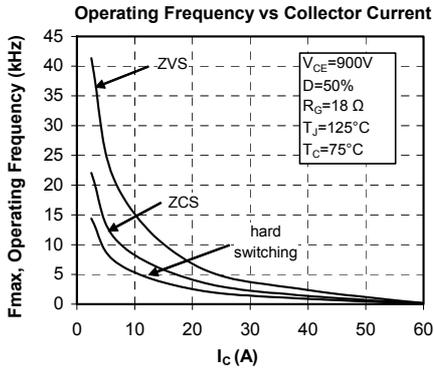
SP3 Package outline (dimensions in mm)



See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

Typical Performance Curve





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